## DG221B <br> New Product <br> Vishay Siliconix

## Quad SPST CMOS Analog Switch with Latches

## FEATURES

- Accepts 150 -ns Write Pulse Width
- 5-V On-Chip Regulator
- Latches Are Transparent with WR Low
- Low On-Resistance: $60 \Omega$

BENEFITS

- Compatible with Most $\mu$ P Buses
- Allows Wide Power Supply Tolerance Without Affecting TTL Compatibility
- Reduced Power Consumption
- Allows Flexibility of Design


## APPLICATIONS

- $\mu$ P Based Systems
- Automatic Test Equipment
- Communication Systems
- Data Acquisition Systems
- Medical Instrumentation
- Factory Automation


## DESCRIPTION

The DG221B is a monolithic quad single-pole, single-throw analog switch designed for precision switching applications in communication, instrumentation and process control systems. Featuring independent onboard latches and a common WR pin, each DG221B can be memory mapped, and addressed as a single data byte for simultaneous switching.

The DG221B combines low power and low on-resistance (60 $\Omega$ typical) while handling continuous currents up to 20 mA . An epitaxial layer prevents latchup.

The device features true bidirectional performance in the on condition.

## FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



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## ABSOLUTE MAXIMUM RATINGS

| Voltages Referenced to V - |  |
| :---: | :---: |
| V+ | 34 V |
| GND . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . 25.25 |  |
| Digital Inputs ${ }^{\text {a }}$, $\mathrm{V}_{\mathrm{S}}, \mathrm{V}_{\mathrm{D}}$ | ( $\mathrm{V}-)-2 \mathrm{~V}$ to ( $\mathrm{V}+$ ) +2 V |
|  | or 20 mA , whichever occurs first |
| Continuous Current (Any Terminal) | 30 mA |
| Continuous Current, S or D | . 20 mA |
| Peak Current, S or D (Pulsed 1 ms , | uty cycle) . . . . . . . . . . . . 70 mA |

Storage Temperature: (DJ and DY Suffix) ............ . -65 to $125^{\circ} \mathrm{C}$
Power Dissipation (Package) ${ }^{\text {b }}$
16-Pin Plastic DIPc . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . 470 mW
16-Pin SOIC ${ }^{\text {d }}$. . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . 600 mW
Notes:
a. Signals on $S_{X}, D_{X}$, or $\mathbb{N}_{X}$ exceeding $V+$ or $V$ - will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
b. All leads welded or soldered to PC Board
c. Derate $6.5 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ above $25^{\circ} \mathrm{C}$
d. Derate $7.7 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ above $75^{\circ} \mathrm{C}$

## SCHEMATIC DIAGRAM (TYPICAL CHANNEL)



FIGURE 1.

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## SPECIFICATIONS ${ }^{a}$

| Parameter | Symbol | Test Conditions Unless Otherwise Specified$\begin{gathered} \mathrm{V}_{+}=15 \mathrm{~V}, \mathrm{~V}-=-15 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{IN}}=2.4 \mathrm{~V}, 0.8^{f} \mathrm{~V}, \overline{\mathrm{WR}}=0 \end{gathered}$ | Temp ${ }^{\text {b }}$ | $\begin{gathered} \text { Limits } \\ -40 \text { to } 85^{\circ} \mathrm{C} \end{gathered}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | Min ${ }^{\text {d }}$ | Typ ${ }^{\text {c }}$ | Max ${ }^{\text {d }}$ |  |

## Analog Switch

| Analog Signal Range ${ }^{\text {e }}$ | $V_{\text {ANALOG }}$ |  | Full | -15 |  | 15 | V |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Drain-Source On-Resistance | ${ }^{\text {r DS }}$ (on) | $\mathrm{I}_{\mathrm{S}}=-10 \mathrm{~mA}, \mathrm{~V}_{\mathrm{D}}= \pm 10 \mathrm{~V}$ | Room Full |  | 60 | $\begin{gathered} 90 \\ 135 \end{gathered}$ | $\Omega$ |
| Source Off Leakage Current | $\mathrm{I}_{\text {(off) }}$ | $\mathrm{V}_{S}= \pm 14 \mathrm{~V}, \mathrm{~V}_{\mathrm{D}}=\mp 14 \mathrm{~V}$ | Room Full | $\begin{gathered} \hline-5 \\ -100 \end{gathered}$ | $\pm 0.01$ | $\begin{gathered} 5 \\ 100 \end{gathered}$ | nA |
| Drain Off <br> Leakage Current | $l_{\text {(off) }}$ |  | Room Full | $\begin{gathered} -5 \\ -100 \end{gathered}$ | $\pm 0.02$ | $\begin{gathered} 5 \\ 100 \end{gathered}$ |  |
| Drain On <br> Leakage Current | $l_{\text {( }}^{\text {(on })}$ | $\mathrm{V}_{S}=\mathrm{V}_{\mathrm{D}}= \pm 14 \mathrm{~V}$ | Room Full | $\begin{gathered} \hline-5 \\ -200 \end{gathered}$ | $\pm 0.01$ | $\begin{gathered} 5 \\ 200 \end{gathered}$ |  |

## Digital Control

| Input Current | $\mathrm{I}_{\text {INL }}, \mathrm{l}_{\text {INH }}$ | $\mathrm{V}_{\mathrm{IN}}=0 \mathrm{~V}$ or $=2.4 \mathrm{~V}$ | Room Full | -1 -10 | -0.0004 | 1 10 | $\mu \mathrm{A}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |

## Dynamic Characteristics

| Turn-On Time | ton | See Figure 2 | Room |  |  | 550 | ns |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Turn-Off Time | toff |  | Room |  |  | 340 |  |
| Turn-On Time Write | ton, $\overline{W R}$ | See Figure 3 | Room |  |  | 550 |  |
| Turn-Off Time Write | $\mathrm{t}_{\text {OFF }}, \overline{\mathrm{WR}}$ |  | Room |  |  | 340 |  |
| Write Pulse Width | tw | See Figure 4 | Room | 150 | 120 |  |  |
| Input Setup Time | ts |  | Room | 180 | 130 |  |  |
| Input Hold Time | $\mathrm{t}_{\mathrm{H}}$ |  | Room | 20 | 18 |  |  |
| Charge Injection | Q | $\begin{gathered} \mathrm{C}_{\mathrm{L}}=1000 \mathrm{pF} \\ \mathrm{~V}_{\mathrm{GEN}}=0 \mathrm{~V}, \mathrm{R}_{\mathrm{GEN}}=0 \Omega \end{gathered}$ | Room |  | 20 |  | pC |
| Source-Off Capacitance | $\mathrm{C}_{\text {S(off) }}$ | $\mathrm{f}=1 \mathrm{MHz}, \mathrm{V}_{\mathrm{S}}, \mathrm{V}_{\mathrm{D}}=0 \mathrm{~V}$ | Room |  | 8 |  | pF |
| Drain-Off Capacitance | $\mathrm{C}_{\mathrm{D} \text { (off) }}$ |  | Room |  | 9 |  |  |
| Channel-On Capacitance | $\mathrm{C}_{\mathrm{D} \text { (on) }}$ |  | Room |  | 29 |  |  |
| Off Isolation | OIRR | $\begin{gathered} \mathrm{V}_{\mathrm{S}}=1 \mathrm{~V}_{\mathrm{p}-\mathrm{p}}, \mathrm{f}=100 \mathrm{kHz} \\ \mathrm{C}_{\mathrm{L}}=15 \mathrm{pF}, \mathrm{R}_{\mathrm{L}}=1 \mathrm{k} \Omega \end{gathered}$ | Room |  | 70 |  | dB |
| Interchannel Crosstalk | $\mathrm{X}_{\text {TALK }}$ |  | Room |  | 90 |  |  |

Power Supplies

| Positive Supply Current | ${ }^{+}$ | All Channels On or Off$\mathrm{V}_{\mathrm{IN}}=0 \mathrm{~V} \text { or } 2.4 \mathrm{~V}$ | Full |  | 0.8 | 1.5 | mA |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Negative Supply Current | I- |  | Room | -1 | -0.4 |  |  |

## Notes:

a. Refer to PROCESS OPTION FLOWCHART.
b. Room $=25^{\circ} \mathrm{C}$, Full $=$ as determined by the operating temperature suffix.
c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
e. Guaranteed by design, not subject to production test.
f. $\quad \mathrm{V}_{\mathrm{IN}}=$ input voltage to perform proper function.

## TEST CIRCUITS



$$
V_{O}=V_{S} \quad \frac{R_{L}}{R_{L}+r_{D S(\text { on })}}
$$

FIGURE 2. Switching Time


$$
V_{O}=V_{S} \quad \frac{R_{L}}{R_{L}+r_{D S(o n)}}
$$

FIGURE 3. $\overline{W R}$ Switching Time


The latches are level sensitive. When $\overline{W R}$ is held low the latches are transparent and the switches respond to the digital inputs. The digital inputs are latched on the rising edge of $\overline{W R}$.

FIGURE 4. $\overline{W R}$ Setup Conditions

## TEST CIRCUITS


$\Delta \mathrm{V}_{\mathrm{O}}=$ measured voltage error due to charge injection The charge injection in coulombs is $\mathrm{Q}=\mathrm{C}_{\mathrm{L}} \times \Delta \mathrm{V}_{\mathrm{O}}$

FIGURE 5. Charge Injection


| $\quad$ Off Isolation $=20 \log$ | $\frac{\mathrm{~V}_{\mathrm{S}}}{\mathrm{V}_{\mathrm{O}}}$ |
| :--- | :--- |
| $\mathrm{C}=\mathrm{RF}$ bypass |  |

FIGURE 6. Off Isolation


| $\quad X_{\text {TALK }}$ Isolation $=20 \log$ | $\left.\frac{V_{S}}{V_{O}} \right\rvert\,$ |
| :--- | :--- |
| $C=$ RF bypass |  |

FIGURE 7. Channel-to-Channel Crosstalk

## APPLICATION HINTS ${ }^{\text {a }}$

| V+ <br> Positive Supply <br> Voltage <br> (V) | V- <br> Negative Supply Voltage (V) | GND <br> (V) | $\overline{W R}$ <br> (V) | $\begin{gathered} \mathrm{V}_{\text {IN }} \\ \text { Logic Input } \\ \text { Voltage } \\ \left.\mathrm{V}_{\mathrm{INH}(\min /} / \mathrm{V}_{\mathrm{INL}(\max )} \mathrm{V}\right) \end{gathered}$ | $V_{S}$ or $V_{D}$ Analog Voltage Range (V) |
| :---: | :---: | :---: | :---: | :---: | :---: |
| 15 | -15 | 0 | 2.4/0.8 | 2.4/0.8 | -15 to 15 |
| 10 | -10 | 0 | 2.4/0.8 | 2.4/0.8 | -10 to 10 |
| 10 | -5 | 0 | 2.4/0.8 | 2.4/0.8 | -5 to 10 |

Notes:
a. Application Hints are for DESIGN AID ONLY, not guaranteed and not subject to production testing.

## APPLICATIONS



FIGURE 8. $\mu$ P-Controlled Analog Signal Attenuator

| TRUTH TABLE |  |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathbf{I N}_{\mathbf{1}}$ | $\mathbf{I N}_{\mathbf{2}}$ | $\mathbf{I N}_{\mathbf{3}}$ | $\mathbf{I N}_{\mathbf{4}}$ | $\mathbf{W R}^{\mathbf{A}}$ | ON SWITCH |
| 0 | 0 | 0 | 0 | 0 | All |
| 1 | 1 | 1 | 1 | 0 | None |
| 0 | 1 | 1 | 1 | 0 | 1 |
| 1 | 0 | 1 | 1 | 0 | 2 |
| 1 | 1 | 0 | 1 | 0 | 3 |
| 1 | 1 | 1 | 0 | 0 | 4 |

## OUTPUT ATTENUATION FOR FIGURE 8

| $\mathbf{W R}$ | $\mathbf{I N}_{\mathbf{1}}$ | $\mathbf{I N}_{\mathbf{2}}$ | $\mathbf{I N}_{\mathbf{3}}$ | $\mathbf{I N}_{\mathbf{4}}$ | Gain |
| :---: | :---: | :---: | :---: | :---: | :---: |
| 0 | 0 | 1 | 1 | 1 | 0.1 |
| 0 | 1 | 0 | 1 | 1 | 0.01 |
| 0 | 1 | 1 | 0 | 1 | 0.001 |
| 0 | 1 | 1 | 1 | 0 | 0.0001 |

Notes:
a. $\overline{W R}$ may be held at " 0 " for temporary operation similar to DG201A/DG201B. With $\overline{W R}$ at " 0 " $S W$ will remain on as long as $I N_{1}$ is held at " 0 ".

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